

02/07/03  
2003039245

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property  
Organization  
International Bureau



(43) International Publication Date  
3 July 2003 (03.07.2003)

PCT

(10) International Publication Number  
**WO 2003/054247 A3**

(51) International Patent Classification<sup>7</sup>: C23C 16/44,  
B08B 5/00, H01L 21/311, 21/3065, 21/3213, 21/00, C23C  
14/56

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(21) International Application Number:  
PCT/JP2002/013002

(81) Designated States (*national*): AE, AG, AL, AM, AT, AU,  
AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU,  
CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH,  
GM, HR, HU, ID, IL, IN, IS, KE, KG, KR, KZ, LC, LK,  
LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX,  
MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SC, SD, SE, SG,  
SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC,  
VN, YU, ZA, ZM, ZW.

(22) International Filing Date:  
12 December 2002 (12.12.2002)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:  
2001-379401 13 December 2001 (13.12.2001) JP  
60/391,622 27 June 2002 (27.06.2002) US

(84) Designated States (*regional*): ARIPO patent (GH, GM,  
KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW),  
Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),  
European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE,  
ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, SI, SK,  
TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ,  
GW, ML, MR, NE, SN, TD, TG).

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**Published:**

— with international search report

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(88) Date of publication of the international search report:  
26 February 2004

*For two-letter codes and other abbreviations, refer to the "Guid-  
ance Notes on Codes and Abbreviations" appearing at the begin-  
ning of each regular issue of the PCT Gazette.*



\*162162\*



\*ACTION\*

WO 2003/054247 A3

(54) Title: CLEANING GAS COMPOSITION FOR SEMICONDUCTOR PRODUCTION EQUIPMENT AND CLEANING  
METHOD USING THE GAS

(57) Abstract: The present invention provides a cleaning gas for semiconductor or equipment for producing semiconductor or liquid  
crystal, comprising a fluorine gas containing 1 vol % or less of oxygen and/or oxygen-containing compound. The cleaning gas of the  
present invention enables an efficient production process of semiconductor device with a high etching rate to improve the cleaning  
efficiency which ensures excellent cost performance.